



6N65

Power MOSFET

6.2A, 650V N-CHANNEL POWER MOSFET

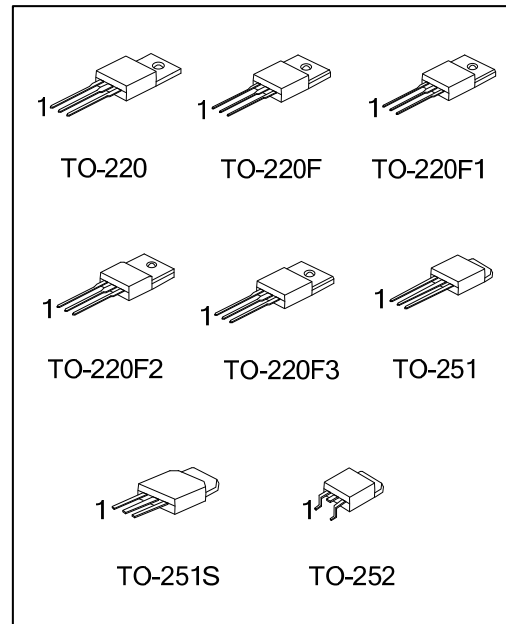
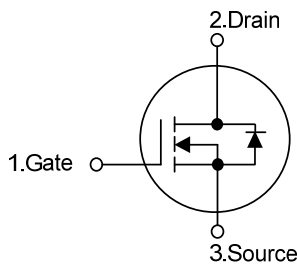
■ DESCRIPTION

The UTC **6N65** is a high voltage power MOSFET designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and high rugged avalanche characteristics. This power MOSFET is usually used in high speed switching applications of switching power supplies and adaptors.

■ FEATURES

- * $R_{DS(ON)} < 1.7\Omega @ V_{GS} = 10V$
- * Fast switching capability
- * Avalanche energy tested
- * Improved dv/dt capability, high ruggedness

■ SYMBOL



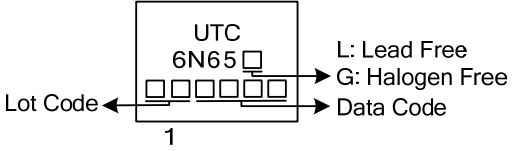
■ ORDERING INFORMATION

| Ordering Number | | Package | Pin Assignment | | | Packing |
|-----------------|--------------|----------|----------------|---|---|-----------|
| Lead Free | Halogen Free | | 1 | 2 | 3 | |
| 6N65L-TA3-T | 6N65G-TA3-T | TO-220 | G | D | S | Tube |
| 6N65L-TF3-T | 6N65G-TF3-T | TO-220F | G | D | S | Tube |
| 6N65L-TF1-T | 6N65G-TF1-T | TO-220F1 | G | D | S | Tube |
| 6N65L-TF2-T | 6N65G-TF2-T | TO-220F2 | G | D | S | Tube |
| 6N65L-TF3T-T | 6N65G-TF3T-T | TO-220F3 | G | D | S | Tube |
| 6N65L-TM3-T | 6N65G-TM3-T | TO-251 | G | D | S | Tube |
| 6N65L-TMS-T | 6N65G-TMS-T | TO-251S | G | D | S | Tube |
| 6N65L-TN3-T | 6N65G-TN3-T | TO-252 | G | D | S | Tube |
| 6N65L-TN3-R | 6N65G-TN3-R | TO-252 | G | D | S | Tape Reel |

Note: Pin Assignment: G: Gate D: Drain S: Source

| | |
|--|--|
| <p>6N65L-TA3-T</p> <p>(1)Packing Type (2)Package Type (3)Lead Free</p> | <p>(1) T: Tube, R: Tape Reel (2) TA3: TO-220, TF3: TO-220F, TF1: TO-220F1, TF2: TO-220F2, TF3T: TO-220F3, TM3: TO-251, TMS: TO-251S, TN3: TO-252 (3) L: Lead Free, G: Halogen Free</p> |
|--|--|

■ MARKING INFORMATION

| PACKAGE | MARKING |
|--|---|
| TO-220 TO-220F TO-220F1 TO-220F2 TO-220F3 TO-251 TO-251S TO-252 |  <p> L: Lead Free G: Halogen Free </p> |

■ ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

| PARAMETER | | SYMBOL | RATINGS | UNIT |
|--------------------------------------|--------------------------|-----------|------------|------------------|
| Drain-Source Voltage | | V_{DSS} | 650 | V |
| Gate-Source Voltage | | V_{GSS} | ± 30 | V |
| Avalanche Current (Note 2) | | I_{AR} | 6.2 | A |
| Continuous Drain Current | | I_D | 6.2 | A |
| Pulsed Drain Current (Note 2) | | I_{DM} | 24.8 | A |
| Avalanche Energy | Single Pulsed (Note 3) | E_{AS} | 440 | mJ |
| Peak Diode Recovery dv/dt (Note 4) | | dv/dt | 4.5 | ns |
| Power Dissipation | TO-220 | P_D | 125 | W |
| | TO-220F/TO-220F1 | | 40 | W |
| | TO-220F3 | | | |
| | TO-220F2 | | 42 | W |
| | TO-251/TO-251S TO-252 | | 55 | W |
| Junction Temperature | | T_J | +150 | $^\circ\text{C}$ |
| Operating Temperature | | T_{OPR} | -55 ~ +150 | $^\circ\text{C}$ |
| Storage Temperature | | T_{STG} | -55 ~ +150 | $^\circ\text{C}$ |

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by T_J

3. $L = 24\text{mH}$, $I_{AS} = 6\text{A}$, $V_{DD} = 90\text{V}$, $R_G = 25\ \Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 6.2\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

| PARAMETER | | SYMBOL | RATING | UNIT | | | |
|--------------------------|---|---------------|------------------------------|---------------------------|---------------|------|---------------------------|
| Junction to Ambient | TO-220/TO-220F TO-220F1/TO-220F2 TO-220F3 | θ_{JA} | 62.5 | $^\circ\text{C}/\text{W}$ | | | |
| | TO-251/TO-251S TO-252 | | | | 110 | | |
| | Junction to Case | | TO-220 | | θ_{JC} | 1.0 | $^\circ\text{C}/\text{W}$ |
| | | | TO-220F/TO-220F1 TO-220F3 | | | 3.2 | |
| | | | TO-220F2 | | | 2.97 | |
| TO-251/TO-251S TO-252 | | 2.27 | | | | | |

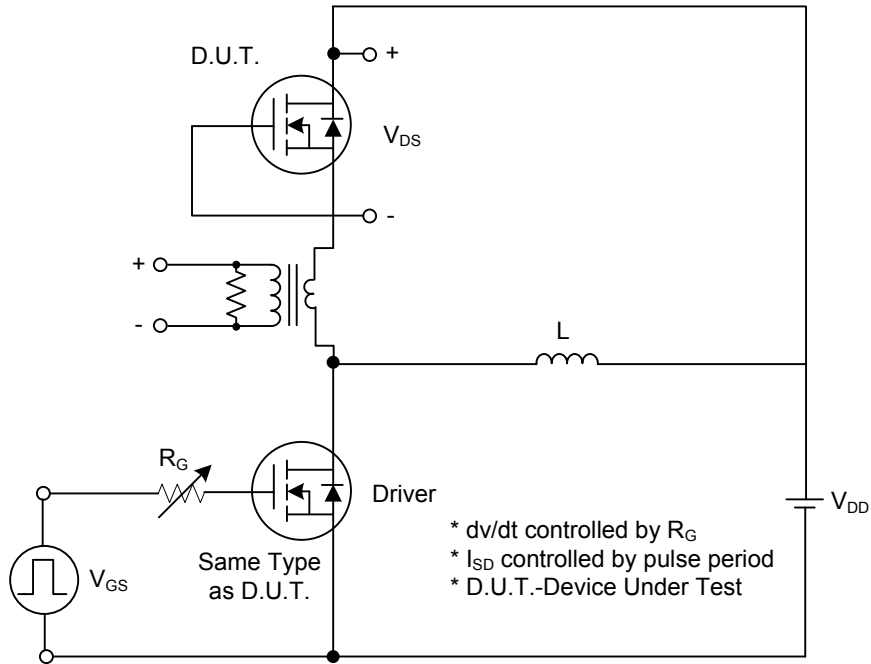
■ ELECTRICAL CHARACTERISTICS ($T_J=25^\circ\text{C}$, unless otherwise specified)

| PARAMETER | SYMBOL | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|---|------------------------------|--|-----|------|------|--------------------|
| OFF CHARACTERISTICS | | | | | | |
| Drain-Source Breakdown Voltage | BV_{DSS} | $V_{GS} = 0V, I_D = 250\mu A$ | 650 | | | V |
| Drain-Source Leakage Current | I_{DSS} | $V_{DS} = 650V, V_{GS} = 0V$ | | | 10 | μA |
| Gate- Source Leakage Current | Forward | I_{GSS} | | | 100 | nA |
| | Reverse | | | | -100 | nA |
| Breakdown Voltage Temperature Coefficient | $\Delta BV_{DSS}/\Delta T_J$ | $I_D=250\mu A$, Referenced to 25°C | | 0.53 | | $V/^\circ\text{C}$ |
| ON CHARACTERISTICS | | | | | | |
| Gate Threshold Voltage | $V_{GS(TH)}$ | $V_{DS} = V_{GS}, I_D = 250\mu A$ | 2.0 | | 4.0 | V |
| Static Drain-Source On-State Resistance | $R_{DS(ON)}$ | $V_{GS} = 10V, I_D = 3.1A$ | | 1.1 | 1.7 | Ω |
| DYNAMIC CHARACTERISTICS | | | | | | |
| Input Capacitance | C_{ISS} | $V_{DS}=25V, V_{GS}=0V,$ $f=1.0\text{ MHz}$ | | 950 | 1200 | pF |
| Output Capacitance | C_{OSS} | | | 95 | 120 | pF |
| Reverse Transfer Capacitance | C_{RSS} | | | 18 | 25 | pF |
| SWITCHING CHARACTERISTICS | | | | | | |
| Turn-On Delay Time | $t_{D(ON)}$ | $V_{DD}=325V, I_D =6.2A,$ $R_G =25\Omega$ (Note 1, 2) | | 45 | 60 | ns |
| Turn-On Rise Time | t_R | | | 100 | 130 | ns |
| Turn-Off Delay Time | $t_{D(OFF)}$ | | | 300 | 400 | ns |
| Turn-Off Fall Time | t_F | | | 220 | 270 | ns |
| Total Gate Charge | Q_G | $V_{DS}=520V, I_D=6.2A,$ $V_{GS}=10V$ (Note 1, 2) | | 180 | 200 | nC |
| Gate-Source Charge | Q_{GS} | | | 8 | | nC |
| Gate-Drain Charge | Q_{GD} | | | 20 | | nC |
| DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS | | | | | | |
| Drain-Source Diode Forward Voltage | V_{SD} | $V_{GS} = 0V, I_S = 6.2A$ | | | 1.4 | V |
| Maximum Continuous Drain-Source Diode Forward Current | I_S | | | | 6.2 | A |
| Maximum Pulsed Drain-Source Diode Forward Current | I_{SM} | | | | 24.8 | A |
| Reverse Recovery Time | t_{RR} | $V_{GS} = 0V, I_S = 6.2A,$ | | 290 | | ns |
| Reverse Recovery Charge | Q_{RR} | $di_F/dt = 100\text{ A}/\mu\text{s}$ (Note 1) | | 2.35 | | μC |

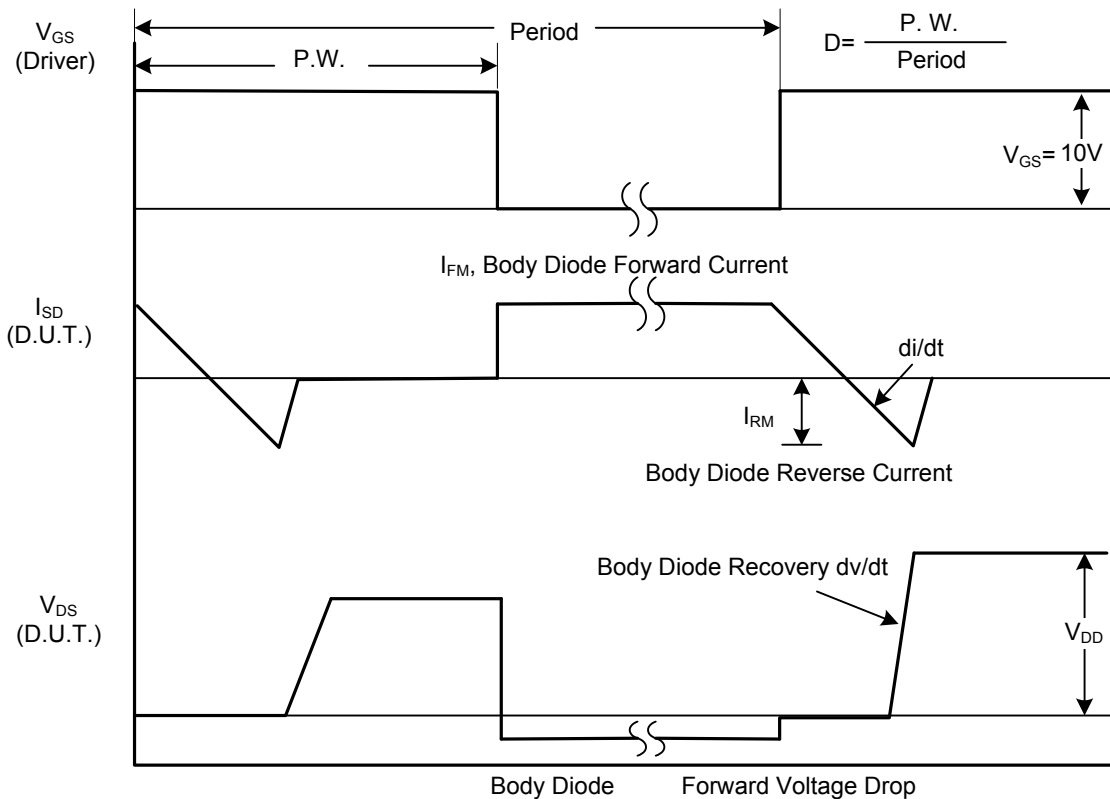
Notes: 1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$

2. Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS

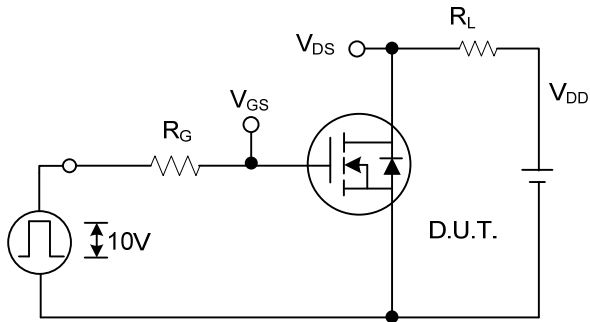


Peak Diode Recovery dv/dt Test Circuit

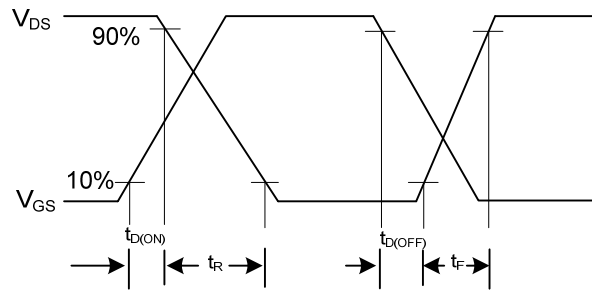


Peak Diode Recovery dv/dt Waveforms

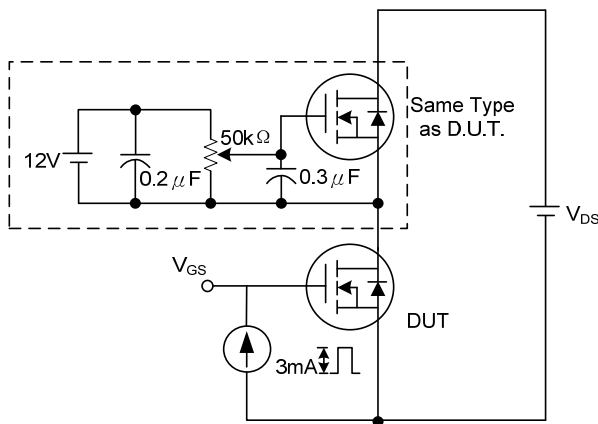
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



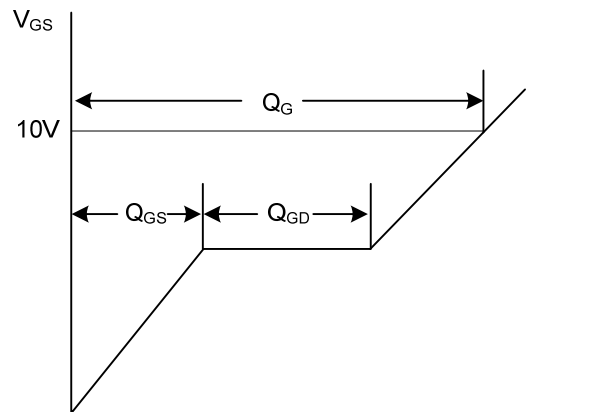
Switching Test Circuit



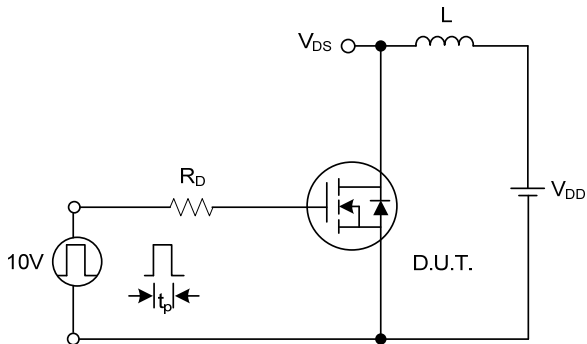
Switching Waveforms



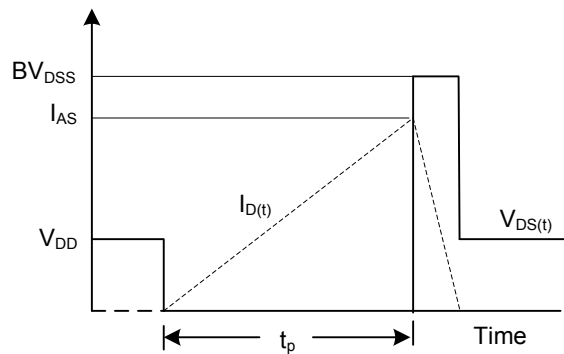
Gate Charge Test Circuit



Charge
Gate Charge Waveform

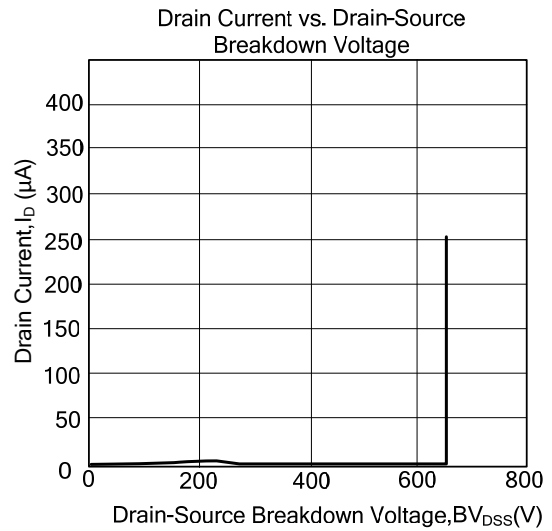
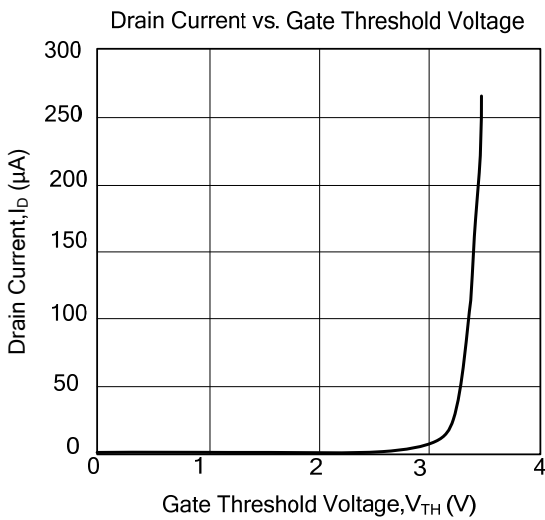
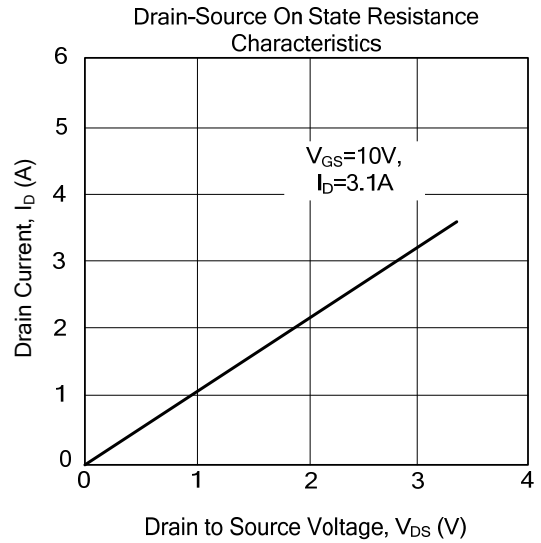
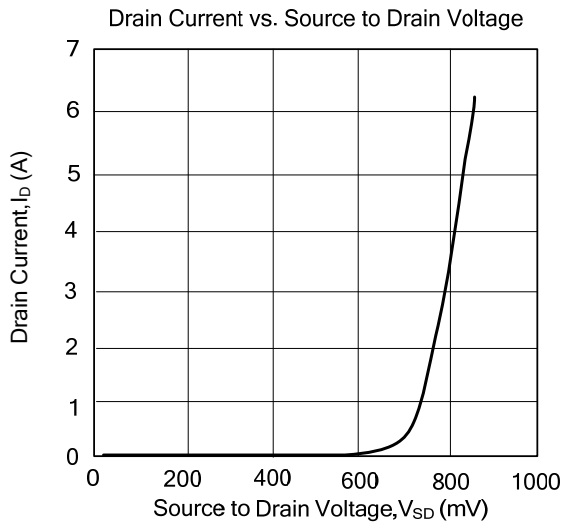


Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS



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